IN THE CLAIMS:

1. (Currently Amended) A liquid crystal display device comprising:

a conductive layer over an insulating surface;

a gate electrode formed on ~~an insulating surface~~ the conductive layer;

a semiconductor film formed on the gate electrode sandwiching an insulating film;

a source region and a drain region formed on the semiconductor film;

a source electrode formed over the source region;

a drain electrode formed over the drain region;

a barrier film formed so as to cover at least portions of ~~ends of~~ an end surface of the source electrode ~~formed on the source region~~, [[a]] an end surface of the drain electrode ~~formed on the drain region, and the source electrode and the drain electrode~~, an end surface of the source region, an end surface of the source region, an end surface of the drain region, and an end surface of the semiconductor film; and

a pixel electrode formed so as to cover the drain electrode and the barrier film,

wherein at least a portion of an end surface of the source region approximately corresponds to an end surface of the semiconductor film and an end surface of the source electrode; and

wherein at least a portion of an end surface of the drain region approximately corresponds to an end surface of the semiconductor film and an end surface of the drain electrode, and

wherein a portion of the conductive layer which is not overlapped with the gate electrode is oxidized and insulated.

2. (Currently Amended) A liquid crystal display device comprising:

a conductive layer over an insulating surface;

a gate electrode formed on ~~an insulating surface~~ the conductive layer;

a semiconductor film formed on the gate electrode sandwiching an insulating film;

a source region and a drain region formed on the semiconductor film;

a source electrode formed over the source region;

a drain electrode formed over the drain region;

a barrier film formed so as to cover at least portions of ~~ends of~~ an end surface of the source electrode ~~formed on the source region~~, [[a]] an end surface of the drain electrode ~~formed on the drain region, and the source electrode and the drain electrode~~, an end surface of the source region, an end surface of the source region, an end surface of the drain region, and an end surface of the semiconductor film; and

a pixel electrode formed so as to cover the drain electrode and the barrier film,

wherein one end surface of the drain region approximately corresponds to an end surface of the semiconductor film and an end surface of the ~~rain~~ drain electrode and the other end surface approximately corresponds to an end surface of the pixel electrode and the other end surface of the drain electrode, and

wherein a portion of the conductive layer which is not overlapped with the gate electrode is oxidized and insulated.

3. (Original) The liquid crystal display device according to claim 1, wherein the pixel electrode is formed of a light-transmitting conductive film.

4. (Original) The liquid crystal display device according to claim 2, wherein the pixel electrode is formed of a light-transmitting conductive film.

5. (Original) The liquid crystal display device according to claim 1, wherein the pixel electrode is formed of a conductive film containing Ag (silver), Au (gold), Cu (copper), W (tungsten), and Al (aluminum) as its main component, or a lamination thereof.

6. (Original) The liquid crystal display device according to claim 2, wherein the pixel electrode is formed of a conductive film containing Ag (silver), Au (gold), Cu (copper), W (tungsten), and Al (aluminum) as its main component, or a lamination thereof.

7. (Original) The liquid crystal display device according to claim 1, wherein the semiconductor film is a semi-amorphous semiconductor containing hydrogen and halogen element, and a crystalline structure.

8. (Original) The liquid crystal display device according to claim 2, wherein the semiconductor film is a semi-amorphous semiconductor containing hydrogen and halogen element, and a crystalline structure.

9. (Currently Amended) A method for manufacturing a liquid crystal display device comprising:

forming a conductive layer over an insulating surface;

forming a gate electrode by selectively ejecting composition on ~~an insulating surface~~ the conductive layer;

oxidizing a portion of the conductive layer which is not overlapped with the gate electrode;

forming an insulating film so as to cover the gate electrode;

forming a first semiconductor film on the insulating film;

forming a second semiconductor film containing an impurity element which imparts N-type or P-type on the first semiconductor film;

forming a first conductive film on the second semiconductor film;

forming a pattern of laminated films of the first semiconductor film, the second semiconductor film and the first conductive film by selectively removing the first semiconductor film, the second semiconductor film and the first conductive film by using a first mask;

forming a second conductive film so as to cover the laminated films; and

forming a source region and a drain region formed of the second semiconductor film, a source electrode and a drain electrode formed of the first conductive film, and a pixel electrode formed of the second conductive film by selectively removing a portion of the first semiconductor film, the second semiconductor film, the first conductive film and the second conductive film.

10. (Currently Amended) A method for manufacturing a liquid crystal display device comprising:

forming a conductive layer over an insulating surface;

forming a gate electrode by selectively ejecting composition on ~~an insulating surface~~ the conductive layer;

oxidizing a portion of the conductive layer which is not overlapped with the gate electrode;

forming an insulating film so as to cover the gate electrode;

forming a first semiconductor film on the insulating film;

forming a second semiconductor film containing an impurity element which imparts N-type or P-type on the first semiconductor film;

forming a first conductive film on the second semiconductor film;

forming a pattern of laminated films of the first semiconductor film, the second semiconductor film and the first conductive film by selectively removing the first semiconductor film, the second semiconductor film and the first conductive film by using a first mask;

forming a barrier film by selectively ejecting composition on an end surface of the laminated films;

forming a second conductive film so as to cover the laminated films and the barrier film; and

forming a source region and a drain region formed of the second semiconductor film, a source electrode and a drain electrode formed of the first conductive film, and a pixel electrode formed of the second conductive film by selectively removing a portion of the first semiconductor film, the second semiconductor film, the first conductive film and the second conductive film.

11. (Original) The method for manufacturing a liquid crystal display device according to claim 9; wherein the insulating film, the first semiconductor film, the second semiconductor film and the first conductive film are formed sequentially without being exposed to atmosphere.

12. (Original) The method for manufacturing a liquid crystal display device according to claim 10; wherein the insulating film, the first semiconductor film, the second semiconductor film and the first conductive film are formed sequentially without being exposed to atmosphere.

13. (Original) A method for manufacturing a liquid crystal display device according to claim 9, wherein the first mask and the second mask are formed by selectively ejecting composition.

14. (Original) A method for manufacturing a liquid crystal display device according to claim 10, wherein the first mask and the second mask are formed by selectively ejecting composition.

15. (Original) The method for manufacturing a liquid crystal display device according to claim 9, wherein the second conductive film is formed by selectively ejecting composition.

16. (Original) The method for manufacturing a liquid crystal display device according to claim 10, wherein the second conductive film is formed by selectively ejecting composition.

17. (Currently Amended) A method for manufacturing a liquid crystal display device comprising:

forming a conductive layer over an insulating surface;

forming a gate electrode by selectively ejecting composition on ~~an insulating surface~~ the conductive layer;

oxidizing a portion of the conductive layer which is not overlapped with the gate electrode;

forming an insulating film so as to cover the gate electrode;

forming a first semiconductor film on the insulating film;

forming a second semiconductor film containing an impurity element which imparts N-type or P-type on the first semiconductor film;

forming a first conductive film by selectively ejecting composition on the second semiconductor film;

forming a pattern of laminated films of the first semiconductor film, the second semiconductor film and the first conductive film by selectively removing the first semiconductor film, the second semiconductor film ~~and the first conductive film~~ by using the first conductive film as a first mask; ~~and~~

forming a second conductive film so as to cover the laminated films; and

forming a source region and a drain region formed of the second semiconductor film, a source electrode and a drain electrode formed of the first conductive film, and a pixel electrode formed of the second conductive film by selectively removing a portion of the first semiconductor film, the second semiconductor film, the first conductive film and the second conductive film by using a mask.

18. (New) The liquid crystal display device according to claim 1, wherein the barrier film is formed of a resin material selected from the group consisting of epoxy resin, acryl resin, phenol resin, novolac resin, melamine resin, and urethane resin.

19. (New) The liquid crystal display device according to claim 2, wherein the barrier film is formed of a resin material selected from the group consisting of epoxy resin, acryl resin, phenol resin, novolac resin, melamine resin, and urethane resin.

20. (New) The method for manufacturing a liquid crystal display device according to claim 10, wherein the barrier film is formed of a resin material selected from the group consisting of epoxy resin, acryl resin, phenol resin, novolac resin, melamine resin, and urethane resin.

21. (New) The liquid crystal display device according to claim 1, wherein the conductive layer comprises a metal material selected from the group consisting of Ti, W, Cr, Al, Ta, Ni, Zr, Hf, V, Ir, Nb, Pd, Pt, Mo, Co, and Rh.

22. (New) The liquid crystal display device according to claim 2, wherein the conductive layer comprises a metal material selected from the group consisting of Ti, W, Cr, Al, Ta, Ni, Zr, Hf, V, Ir, Nb, Pd, Pt, Mo, Co, and Rh.

23. (New) The liquid crystal display device according to claim 1, wherein the conductive layer is formed by sputtering or vapor deposition.

24. (New) The liquid crystal display device according to claim 2, wherein the conductive layer is formed by sputtering or vapor deposition.

25. (New) The method for manufacturing a liquid crystal display device according to claim 9, wherein the conductive layer comprises a metal material selected from the group consisting of Ti, W, Cr, Al, Ta, Ni, Zr, Hf, V, Ir, Nb, Pd, Pt, Mo, Co, and Rh.

26. (New) The method for manufacturing a liquid crystal display device according to claim 10, wherein the conductive layer comprises a metal material selected from the group consisting of Ti, W, Cr, Al, Ta, Ni, Zr, Hf, V, Ir, Nb, Pd, Pt, Mo, Co, and Rh.

27. (New) The method for manufacturing a liquid crystal display device according to claim 17, wherein the conductive layer comprises a metal material selected from the group consisting of Ti, W, Cr, Al, Ta, Ni, Zr, Hf, V, Ir, Nb, Pd, Pt, Mo, Co, and Rh.

28. (New) The method for manufacturing a liquid crystal display device according to claim 9, wherein the conductive layer is formed by sputtering or vapor deposition.

29. (New) The method for manufacturing a liquid crystal display device according to claim 10, wherein the conductive layer is formed by sputtering or vapor deposition.

30. (New) The method for manufacturing a liquid crystal display device according to claim 17, wherein the conductive layer is formed by sputtering or vapor deposition.